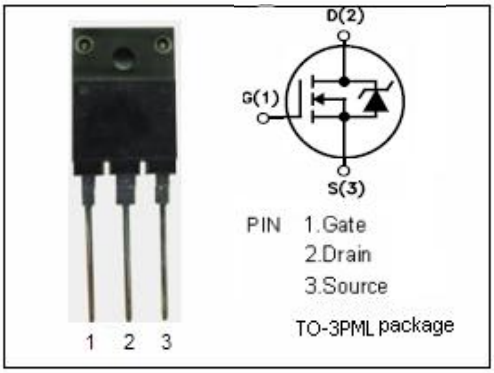
isc N-Channel MOSFET Transistor 2SK765A

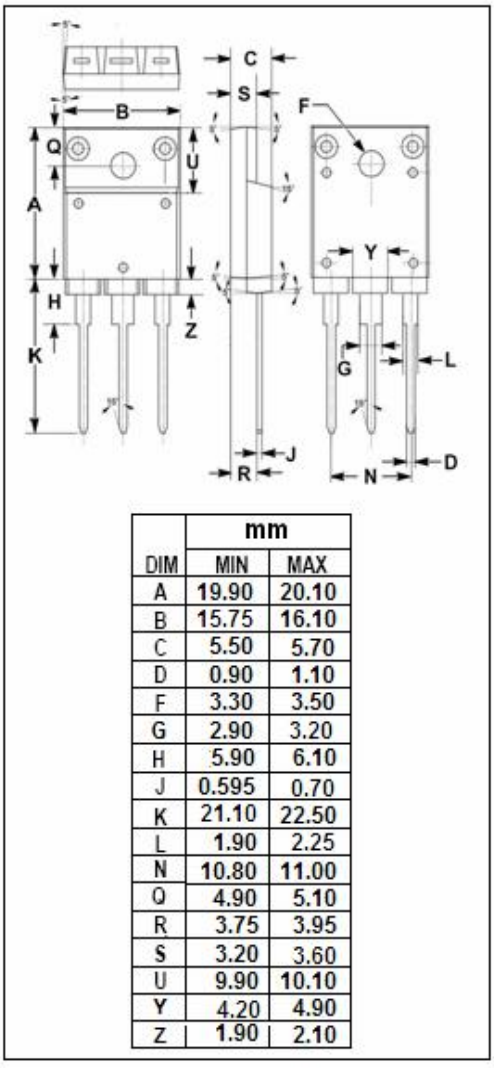


DESCRIPTION

- Drain Current –I_D= 10A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 450V(Min)
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	450	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	10	A
P_{tot}	Total Dissipation@TC=25℃	100	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.0	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W

isc N-Channel Mosfet Transistor 2SK765A

• ELECTRICAL CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	450			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=25 V; I_D=1mA	1.0		5.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	V_{GS}=10V; I_D= 5A		0.5	0.75	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0			±1	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=320V; V_{GS}= 0			100	uA
V_{SD}	Diode Forward Voltage	I_F=10A; V_{GS}=0		1.2		V